

# MJD2955, NJVMJD2955T4G (PNP) MJD3055, NJVMJD3055T4G (NPN)

## Complementary Power Transistors

### DPAK For Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

#### Features

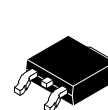
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves (“-1” Suffix)
- Electrically Similar to MJE2955 and MJE3055
- DC Current Gain Specified to 10 Amperes
- High Current Gain-Bandwidth Product –  $f_T = 2.0 \text{ MHz (Min) @ } I_C = 500 \text{ mAdc}$
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings:
  - ◆ Human Body Model, 3B > 8000 V
  - ◆ Machine Model, C > 400 V
- AEC-Q101 Qualified and PPAP Capable
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Packages\*



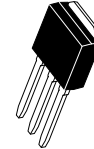
ON Semiconductor®

<http://onsemi.com>

SILICON  
POWER TRANSISTORS  
10 AMPERES  
60 VOLTS, 20 WATTS

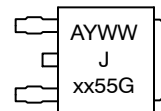


DPAK  
CASE 369C  
STYLE 1

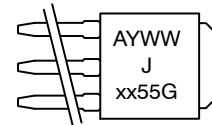


IPAK  
CASE 369D  
STYLE 1

#### MARKING DIAGRAMS



DPAK



IPAK

A = Assembly Location  
Y = Year  
WW = Work Week  
Jxx55 = Device Code  
x = 29 or 30  
G = Pb-Free Package

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MJD2955, NJVMJD2955T4G (PNP) MJD3055, NJVMJD3055T4G (NPN)

## MAXIMUM RATINGS

| Rating                                                                                            | Symbol         | Max           | Unit                     |
|---------------------------------------------------------------------------------------------------|----------------|---------------|--------------------------|
| Collector–Emitter Voltage                                                                         | $V_{CEO}$      | 60            | Vdc                      |
| Collector–Base Voltage                                                                            | $V_{CB}$       | 70            | Vdc                      |
| Emitter–Base Voltage                                                                              | $V_{EB}$       | 5             | Vdc                      |
| Collector Current                                                                                 | $I_C$          | 10            | Adc                      |
| Base Current                                                                                      | $I_B$          | 6             | Adc                      |
| Total Power Dissipation<br>@ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$          | $P_{D\dagger}$ | 20<br>0.16    | W<br>W/ $^\circ\text{C}$ |
| Total Power Dissipation (Note 1)<br>@ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$          | 1.75<br>0.014 | W<br>W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range                                                  | $T_J, T_{stg}$ | -55 to +150   | $^\circ\text{C}$         |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

## THERMAL CHARACTERISTICS

| Characteristic                                   | Symbol          | Max  | Unit                      |
|--------------------------------------------------|-----------------|------|---------------------------|
| Thermal Resistance, Junction–to–Case             | $R_{\theta JC}$ | 6.25 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction–to–Ambient (Note 2) | $R_{\theta JA}$ | 71.4 | $^\circ\text{C}/\text{W}$ |

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                                                                                                                               |                |    |           |                 |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------|----|-----------|-----------------|
| Collector–Emitter Sustaining Voltage (Note 3)<br>( $I_C = 30\text{ mAdc}, I_B = 0$ )                                                                                          | $V_{CEO(sus)}$ | 60 | –         | Vdc             |
| Collector Cutoff Current ( $V_{CE} = 30\text{ Vdc}, I_B = 0$ )                                                                                                                | $I_{CEO}$      | –  | 50        | $\mu\text{Adc}$ |
| Collector Cutoff Current<br>( $V_{CE} = 70\text{ Vdc}, V_{EB(off)} = 1.5\text{ Vdc}$ )<br>( $V_{CE} = 70\text{ Vdc}, V_{EB(off)} = 1.5\text{ Vdc}, T_C = 150^\circ\text{C}$ ) | $I_{CEX}$      | –  | 0.02<br>2 | mAdc            |
| Collector Cutoff Current<br>( $V_{CB} = 70\text{ Vdc}, I_E = 0$ )<br>( $V_{CB} = 70\text{ Vdc}, I_E = 0, T_C = 150^\circ\text{C}$ )                                           | $I_{CBO}$      | –  | 0.02<br>2 | mAdc            |
| Emitter Cutoff Current ( $V_{BE} = 5\text{ Vdc}, I_C = 0$ )                                                                                                                   | $I_{EBO}$      | –  | 0.5       | mAdc            |

### ON CHARACTERISTICS

|                                                                                                                                                    |               |         |          |     |
|----------------------------------------------------------------------------------------------------------------------------------------------------|---------------|---------|----------|-----|
| DC Current Gain (Note 3)<br>( $I_C = 4\text{ Adc}, V_{CE} = 4\text{ Vdc}$ )<br>( $I_C = 10\text{ Adc}, V_{CE} = 4\text{ Vdc}$ )                    | $h_{FE}$      | 20<br>5 | 100<br>– | –   |
| Collector–Emitter Saturation Voltage (Note 3)<br>( $I_C = 4\text{ Adc}, I_B = 0.4\text{ Adc}$ )<br>( $I_C = 10\text{ Adc}, I_B = 3.3\text{ Adc}$ ) | $V_{CE(sat)}$ | –       | 1.1<br>8 | Vdc |
| Base–Emitter On Voltage (Note 3)<br>( $I_C = 4\text{ Adc}, V_{CE} = 4\text{ Vdc}$ )                                                                | $V_{BE(on)}$  | –       | 1.8      | Vdc |

### DYNAMIC CHARACTERISTICS

|                                                                                                             |       |   |   |     |
|-------------------------------------------------------------------------------------------------------------|-------|---|---|-----|
| Current–Gain – Bandwidth Product<br>( $I_C = 500\text{ mAdc}, V_{CE} = 10\text{ Vdc}, f = 500\text{ kHz}$ ) | $f_T$ | 2 | – | MHz |
|-------------------------------------------------------------------------------------------------------------|-------|---|---|-----|

3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

## MJD2955, NJVMJD2955T4G (PNP) MJD3055, NJVMJD3055T4G (NPN)

### ORDERING INFORMATION

| Device        | Package Type      | Package | Shipping <sup>†</sup> |
|---------------|-------------------|---------|-----------------------|
| MJD2955G      | DPAK<br>(Pb-Free) | 369C    | 75 Units / Rail       |
| MJD2955-1G    | IPAK<br>(Pb-Free) | 369D    | 75 Units / Rail       |
| MJD2955T4G    | DPAK<br>(Pb-Free) | 369C    | 2,500 Tape & Reel     |
| NJVMJD2955T4G | DPAK<br>(Pb-Free) | 369C    | 2,500 Tape & Reel     |
| MJD3055G      | DPAK<br>(Pb-Free) | 369C    | 75 Units / Rail       |
| MJD3055T4G    | DPAK<br>(Pb-Free) | 369C    | 2,500 Tape & Reel     |
| NJVMJD3055T4G | DPAK<br>(Pb-Free) | 369C    | 2,500 Tape & Reel     |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

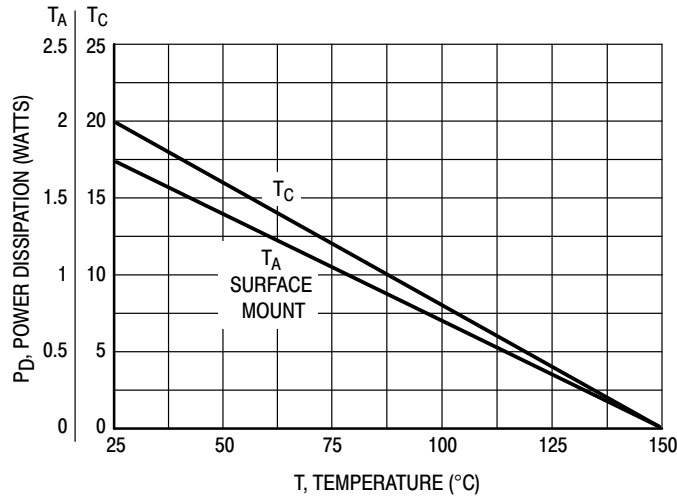


Figure 1. Power Derating

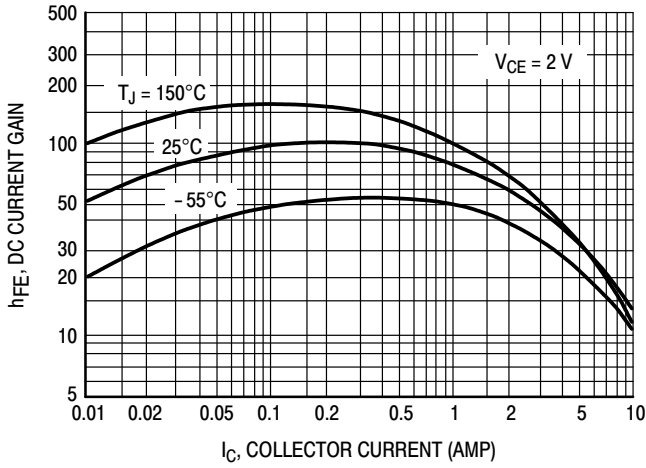


Figure 2. DC Current Gain

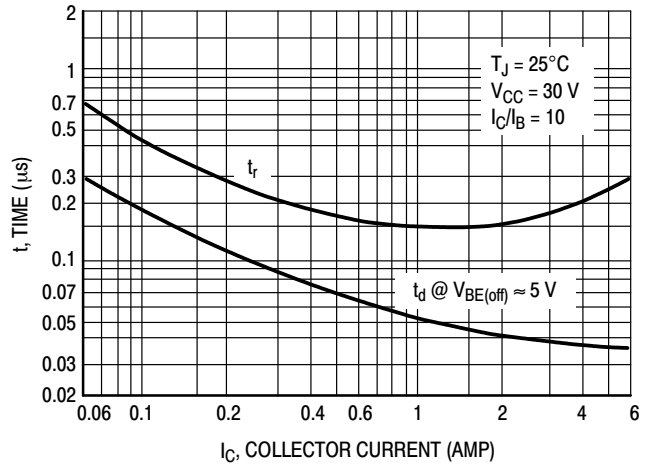


Figure 3. Turn-On Time

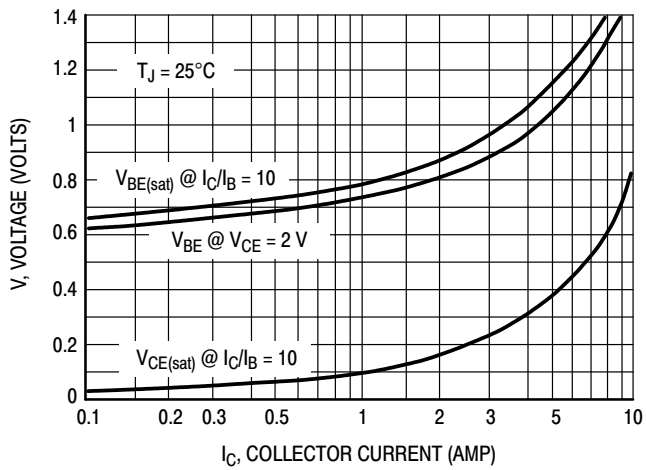


Figure 4. "On" Voltages, MJD3055

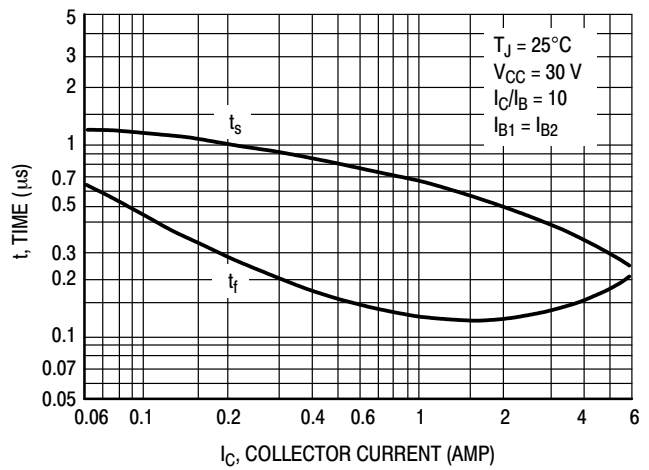


Figure 5. Turn-Off Time

# MJD2955, NJVMJD2955T4G (PNP) MJD3055, NJVMJD3055T4G (NPN)

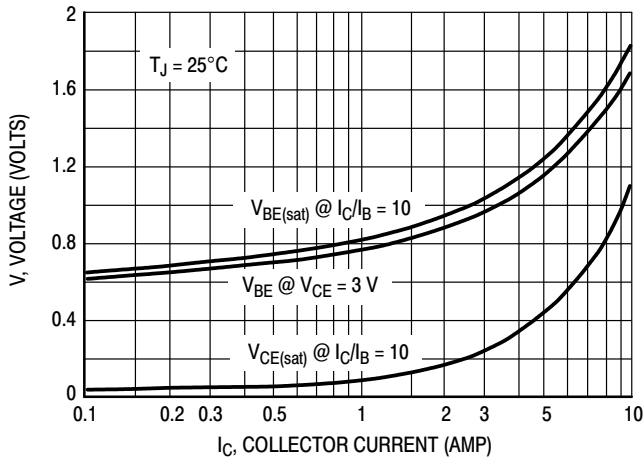


Figure 6. "On" Voltages, MJD2955

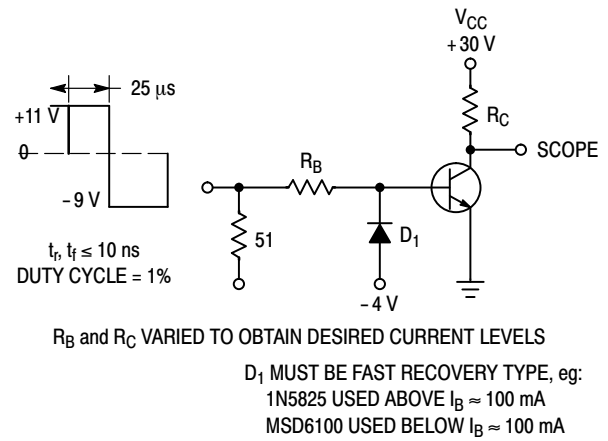


Figure 7. Switching Time Test Circuit

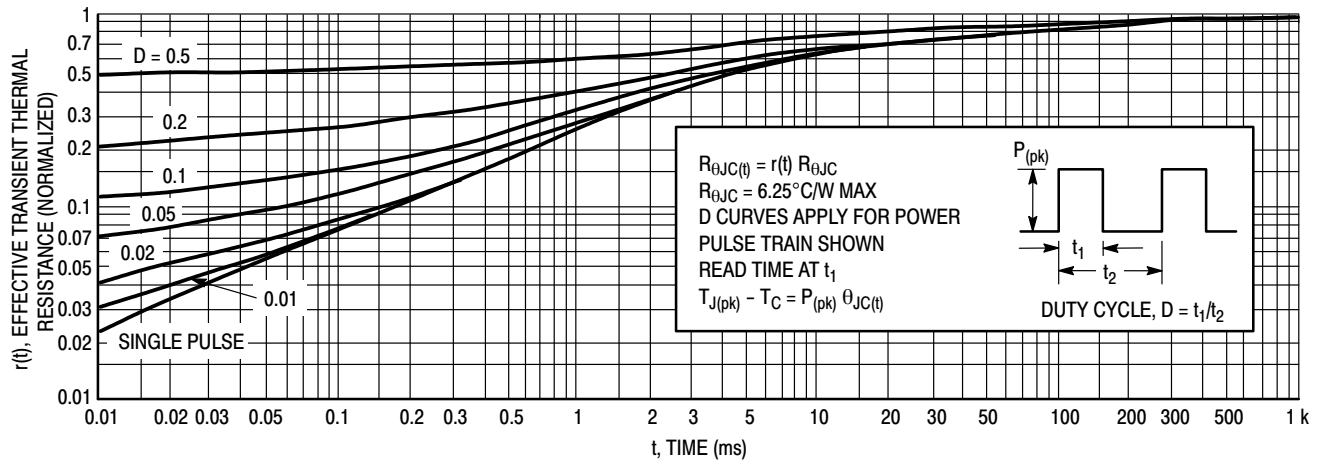


Figure 8. Thermal Response

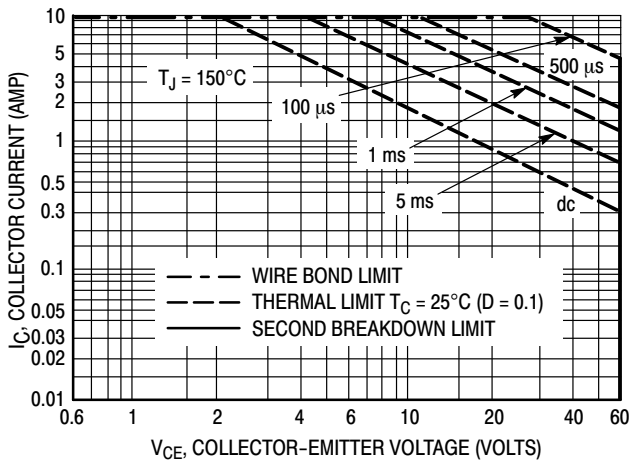


Figure 9. Maximum Forward Bias Safe Operating Area

## FORWARD BIAS SAFE OPERATING AREA INFORMATION

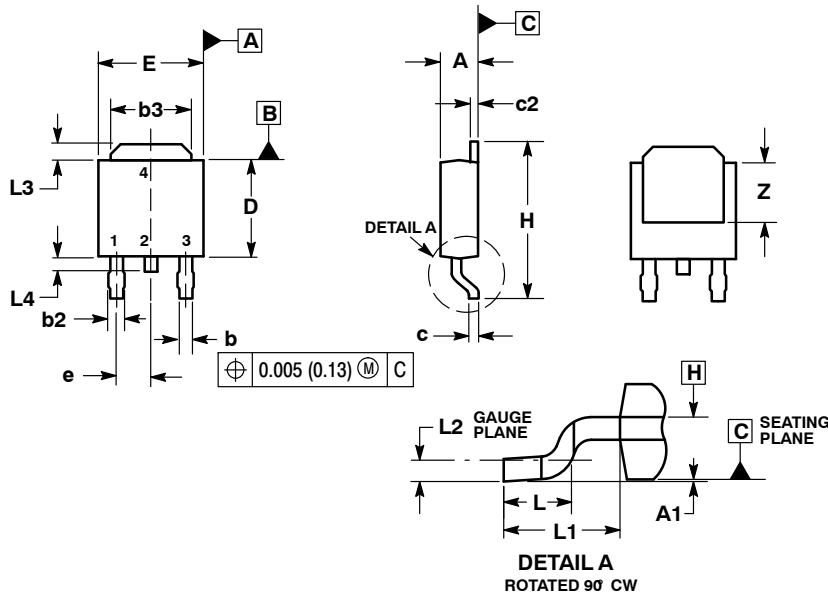
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# MJD2955, NJVMJD2955T4G (PNP) MJD3055, NJVMJD3055T4G (NPN)

## PACKAGE DIMENSIONS

### DPAK CASE 369C-01 ISSUE D

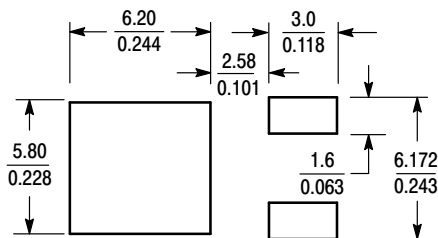


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 0.086  | 0.094 | 2.18        | 2.38  |
| A1  | 0.000  | 0.005 | 0.00        | 0.13  |
| b   | 0.025  | 0.035 | 0.63        | 0.89  |
| b2  | 0.030  | 0.045 | 0.76        | 1.14  |
| b3  | 0.180  | 0.215 | 4.57        | 5.46  |
| c   | 0.018  | 0.024 | 0.46        | 0.61  |
| c2  | 0.018  | 0.024 | 0.46        | 0.61  |
| D   | 0.235  | 0.245 | 5.97        | 6.22  |
| E   | 0.250  | 0.265 | 6.35        | 6.73  |
| e   | 0.090  | BSC   | 2.29        | BSC   |
| H   | 0.370  | 0.410 | 9.40        | 10.41 |
| L   | 0.055  | 0.070 | 1.40        | 1.78  |
| L1  | 0.108  | REF   | 2.74        | REF   |
| L2  | 0.020  | BSC   | 0.51        | BSC   |
| L3  | 0.035  | 0.050 | 0.89        | 1.27  |
| L4  | ---    | 0.040 | ---         | 1.01  |
| Z   | 0.155  | ---   | 3.93        | ---   |

### SOLDERING FOOTPRINT\*



SCALE 3:1 (mm/inches)

**STYLE 1:**

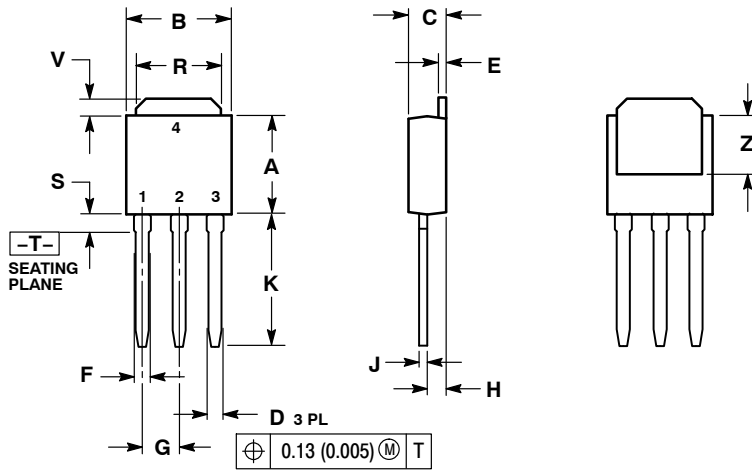
1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MJD2955, NJVMJD2955T4G (PNP) MJD3055, NJVMJD3055T4G (NPN)

## PACKAGE DIMENSIONS


IPAK  
CASE 369D-01  
ISSUE C



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES |       | MILLIMETERS |      |
|-----|--------|-------|-------------|------|
|     | MIN    | MAX   | MIN         | MAX  |
| A   | 0.235  | 0.245 | 5.97        | 6.35 |
| B   | 0.250  | 0.265 | 6.35        | 6.73 |
| C   | 0.086  | 0.094 | 2.19        | 2.38 |
| D   | 0.027  | 0.035 | 0.69        | 0.88 |
| E   | 0.018  | 0.023 | 0.46        | 0.58 |
| F   | 0.037  | 0.045 | 0.94        | 1.14 |
| G   | 0.090  | BSC   | 2.29        | BSC  |
| H   | 0.034  | 0.040 | 0.87        | 1.01 |
| J   | 0.018  | 0.023 | 0.46        | 0.58 |
| K   | 0.350  | 0.380 | 8.89        | 9.65 |
| R   | 0.180  | 0.215 | 4.45        | 5.45 |
| S   | 0.025  | 0.040 | 0.63        | 1.01 |
| V   | 0.035  | 0.050 | 0.89        | 1.27 |
| Z   | 0.155  | ---   | 3.93        | ---  |

- STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

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